

## TABLE OF CONTENTS

Conference Chairs and Technical Program Committee .....	iii
Preface .....	v
Facts about the Electrochemical Society .....	viii
Table of Contents .....	ix

### Session 1 PLENARY SESSION

Ultra-Thin Gate SiO <sub>2</sub> Technology* .....	3
<i>H. Iwai, H. S. Momose, and S.-I. Ohmi</i>	
Scaling of Gate Dielectrics for Advanced CMOS Applications* .....	19
<i>T.-P. Ma</i>	
Defect Generation and Reliability of Ultra-Thin SiO <sub>2</sub> at Low Voltage* .....	33
<i>J. H. Stathis and D. J. DiMaria</i>	

### Session 2 OXIDE TECHNOLOGY I

Deuterium/Hydrogen Isotope Effect and Processing for CMOS Technologies* .....	47
<i>I. Kizilyalli</i>	
Dynamics of Thermal Growth of Silicon Oxide Films on Si .....	57
<i>R. M. C. de Almeida, S. Gonçalves, I. J. R. Baumvol, and F. C. Stedile</i>	
Growth Mechanism of SiO <sub>2</sub> Ultra-Thin Film on Si(100) by Highly Concentrated Ozone Supplied at Low and High Pressure Conditions .....	67
<i>S. Ichimura, K. Nakamura, A. Kurokawa, H. Itoh, and K. Koike</i>	
Electrical Characterization of Thin Oxides Grown on Deuterium Implanted Silicon Substrate* .....	79
<i>D. Misra and R. K. Jarwal</i>	
Oxide Surface Roughness During Stepwise Wet Etching of Fowler-Nordheim Stressed Silicon Dioxide Films .....	89
<i>K. Yamabe, K. Liao, and M. Murata</i>	
Oxidation of Si(001) Surface and Formation of Si/SiO <sub>2</sub> Interface .....	97
<i>T. Uchiyama, T. Uda, and K. Terakura</i>	

\* Invited Paper

**Session 3**  
**OXIDE TECHNOLOGY II**

Improvement of Gate Oxide Integrity by Preparing Atomic Order ..... 101 Flattened Si (100) Surface <i>O. Nakamura, T. Ohkawa, and T. Ohmi</i>	101
Low-Temperature Formation of Gate-Grade Silicon Oxide Films ..... 113 Using High-Density Krypton Plasma <i>Y. Saito, K. Sekine, M. Hirayama, and T. Ohmi</i>	113
Gate Oxide Thinning in MOS Structures with Shallow Trench Isolation .... 125 <i>N. Balasubramanian, E. Johnson, C. Perera, C.-S. Mian, T.-T. Sheng, I. V. Peidous, G. Ping, A. Cuthbertson, and R. Sundaresan</i>	125
Characterization of Oxynitride Dielectric Films Grown in NO/O <sub>2</sub> ..... 131 Mixtures by Rapid Thermal Oxynitridation <i>S. C. Everist, T. L. Meisenheimer, G. C. Nelson, P. M. Smith R. Sharangpani, and S.-P. Tay</i>	131

**Session 4**  
**NITROGEN AND OXYNITRIDES I**

Effect of Fermi Level Position of Polysilicon Gate on the Flatband ..... 145 Voltage Shift for Ultrathin Oxide-Nitride Gate Stacks <i>Z. Wang, D. W. Hodge, R. T. Croswell, and J. R. Hauser</i>	145
Electrical Characterization of Interfacial Reactions in Ti-SiO <sub>2</sub> -Si MOS ..... 153 Structures During Post-Metallization Anneal <i>L.-Å. Ragnarsson, A. Hector, and P. Lundgren</i>	153
Electron Paramagnetic Resonance Study of Defects at Nitric Oxide ..... 161 Treated Si/SiO <sub>2</sub> and Si/Si <sub>3</sub> N <sub>4</sub> Interfaces <i>J. L. Cantin and H.-J. von Bardeleben</i>	161
Compositional and Electrical Differences of SiO <sub>2</sub> /SiC and SiO <sub>2</sub> /Si ..... 169 Structures Upon Thermal Annealing in N <sub>2</sub> O and NO <i>F. C. Stedile, C. Radtke, I. J. R. Baumvol, H. Boudinov, K. McDonald, M. B. Huang, R. A. Weller, L. C. Feldman, and J. R. Williams</i>	169

**Session 5**  
**NITROGEN AND OXYNITRIDES II**

Chemical Structures of Oxynitride/Si(100) Interface ..... 181 <i>K. Takahashi, H. Nohira, H. Kato, N. Tamura, K. Hikazutani, S. Sano, and T. Hattori</i>	181
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Hyperthermal Nitridation for Ultrathin Silicon Oxynitride .....	187
Gate Dielectrics	
<i>C. Krug, I. J. R. Baumvol, F. C. Stedile, M. L. Green, F. Klemens,</i>	
<i>P. J. Silverman, T. W. Sorsch, F. Alvarez, P. Hammer, and</i>	
<i>N. M. Victoria</i>	
Nitrogen Implantation Effects on Ultra-Thin Gate Oxide Grown on .....	199
Nitrogen-Implanted Silicon	
<i>I.-H. Nam, S. I. Hong, J. S. Sim, B.-G. Park, J. D. Lee,</i>	
<i>S.-W. Lee, M.-S. Kang, Y.-W. Kim, and K.-P. Suh</i>	
Characterization of Ultrathin Oxide Interfaces ( $T_{ox} < 1$ nm) .....	209
in Oxide-Nitride Stack Formed by Remote Plasma Enhanced Chemical	
Vapor Deposition	
<i>Z. Wang, S. Wang, W. Li, C. Young, R. T. Croswell, and</i>	
<i>J. R. Hauser</i>	

**Session 6**  
**SILICA AND HYDROGEN**

Silica: A Geochemist's Perspective* .....	217
<i>J. D. Rimstidt</i>	
Hydrogen in Buried SiO <sub>2</sub> Layers .....	235
<i>A. G. Revesz, R. E. Stahlbush, and H. L. Hughes</i>	
Epitaxially Ordered Structure in the Buried Oxide Layer of SIMOX .....	241
Wafers	
<i>T. Shimura, T. Hosoi, and M. Umeno</i>	
Theoretical Study of Oxygen Radicals Impacting Hydrogen-Terminated ....	251
Silicon Surfaces	
<i>A. Tachibana</i>	

**Session 7**  
**MODELING AND SIMULATION**

<i>Ab-Initio</i> Approach on Defect Dynamics in SiO <sub>2</sub> Induced by .....	261
Electronic Excitations*	
<i>Y. Miyamoto and A. Yokozawa</i>	
Model Interface Between Silicon and Disordered SiO <sub>2</sub> .....	271
<i>A. Pasquarello and M. S. Hybertsen</i>	
Atomic Structure and Hyperfine Spectrum of P <sub>b</sub> -Type Defects .....	283
at Si-SiO <sub>2</sub> Interfaces: An <i>Ab-Initio</i> Investigation	
<i>A. Stirling, A. Pasquarello, J.-C. Charlier, and R. Car</i>	

\* Invited Paper

Electronic Structures of SiO <sub>2</sub> /Si(001) Interfaces .....	295
<i>T. Yamasaki, C. Kaneta, T. Uchiyama, T. Uda, and K. Terakura</i>	
Incorporation and Electronics States of a Carbon Atom in SiO <sub>2</sub> .....	307
As Examined Through Calculations from First Principles	
<i>T. Maruizumi and J. Ushio</i>	
Large-Scale Modeling of SiO <sub>2</sub> /Si(011) Interface Structures by Using .....	319
a Novel Inter-Atomic Interaction Model	
<i>T. Watanabe and I. Ohdomari</i>	

**Session 8**  
**OXIDE RELIABILITY I**

Soft and Hard Breakdown of Ultrathin SiO <sub>2</sub> Gate Oxides* .....	333
<i>J. Suñé and E. Miranda</i>	
The Origin and the Creation Mechanism of Positive Charges .....	345
in Silicon Oxide Films	
<i>K. Ohmori, H. Ikeda, A. Sakai, S. Zaima, and Y. Yasuda</i>	
A New Methodology for a Statistical Evaluation of SILC: .....	353
Characterization of Stress Conditions and Oxide Technology	
<i>G. Ghidini, M. Rigamonti, D. Brazelli, F. Pellizzer, A. Martinelli,</i> <i>and N. Galbiati</i>	
Physics and Prospects of Sub-2 nm Oxides* .....	365
<i>M. A. Alam, B. Weir, P. Silverman, J. Bude, A. Ghetti, Y. Ma,</i> <i>M. M. Brown, D. Hwang, and A. Hamad</i>	
Reliability of Gate Oxides on Silicon Substrates with 5-10 nm Oxide .....	377
Thickness	
<i>A. Huber, J. Grabmeier, U. Lambert, and R. Wahlich</i>	
Degradation of Gate Oxide Integrity due to Ni and Cu Contamination .....	387
and Impurity Gettering in Epitaxial Si Wafers	
<i>S. Koveshnikov, D. Beauchaine, Z. Radzimski, and V. Higgs</i>	

**Session 9**  
**OXIDE RELIABILITY II**

Study of Soft Breakdown in Thin SiO <sub>2</sub> Films by Carrier-Separation .....	399
Technique and Breakdown-Transient Modulation*	
<i>A. Toriumi, S. Takagi, and H. Satake</i>	
Soft Breakdown Mechanism in Ultrathin Gate Oxides .....	409
<i>W. Mizubayashi, H. Itokawa, S. Miyazaki, and M. Hirose</i>	

\* Invited Paper

Native and Stress-Induced Traps in SiO <sub>2</sub> Films .....	419
<i>A. Ghetti, M. A. Alam, J. Bude, E. Sangiorgi, G. Timp, and G. Weber</i>	

**Session 10**  
**OXIDE CHARACTERIZATION**

The Conductance Technique: A Method to Separate and Characterize* .....	431
Interface States	
<i>M. J. Uren</i>	
Extending Standard Methods of Characterization to Very Thin Oxides .....	443
<i>A. Balasinski and K. Ramkumar</i>	
Strained Si Layers at Dielectric/Si(100) Interface Probed by X-Ray .....	453
Photoelectron Spectroscopy	
<i>Z. H. Lu, Y. Ma, F. Li, and C. T. Liu</i>	
Pulsed ESR Characterization of SiO <sub>2</sub> Thin Layers on Si .....	459
<i>J. Isoya, S. Yamasaki, K. Tanaka, Y. Kamigaki, T. Kobayashi, Y. Morita, and N. Morishita</i>	

**Session 11**  
**ALTERNATIVE DIELECTRICS**

Silicate Gate Dielectrics for Scaled CMOS* .....	463
<i>G. D. Wilk and R. M. Wallace</i>	
Physical Characterization of Ultrathin Films of High Dielectric Constant ...	477
Materials on Silicon	
<i>E. P. Gusev, M. Copel, E. Cartier, D. Buchanan, H. Okorn-Schmidt, M. A. Gribelyuk, D. Falcon, R. Murphy, S. Molis, I. J. R. Baumvol, C. Krug, M. Jussila, M. Tuominen, and S. Haukka</i>	
Electrical Performance of Stacked High- $\kappa$ Gate Dielectrics: .....	487
Remote Plasma CVD Ta <sub>2</sub> O <sub>5</sub> and (Ta <sub>2</sub> O <sub>5</sub> ) <sub>x</sub> (SiO <sub>2</sub> ) <sub>1-x</sub> Alloys with Ultrathin Plasma Processed SiO <sub>2</sub> Interface Layers	
<i>H. Niimi, R. S. Johnson, G. Lucovsky, and H. Z. Massoud</i>	
Electrical Performance of MOS Devices with Plasma Deposited .....	495
ZrO <sub>2</sub> -SiO <sub>2</sub> Pseudo-Binary Silicate Alloys	
<i>R. Therrien, B. Rayner, and G. Lucovsky</i>	
Characterization of Bulk and Interface Properties of Dielectric Layers .....	505
and Stacks	
<i>H. F. Okorn-Schmidt, E. P. Gusev, D. A. Buchanan, E. Cartier, S. Guha, N. A. Bojarczuk, D. L. Rath, A. Callegari, M. Gribelyuk, and M. Copel</i>	

\* Invited Paper

Light Emission from Interface Traps in SiC MOSFETs .....	513
<i>R. E. Stahlbush and G. G. Jernigan</i>	
Effects of Re-Oxidation on the Electrical Properties of Wet Oxide .....	523
Grown on C-Face of 4H-SiC	
<i>R. K. Chanana and M. E. Zvanut</i>	
<b>Author Index</b> .....	<b>529</b>
<b>Subject Index</b> .....	<b>535</b>